

isc Silicon PNP Power Transistors

3AD53

DESCRIPTION

- DC Current Gain-
: $h_{FE}=20-140@I_C=-4A$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)}=-1.0V(Max)@ I_C=-4A$

APPLICATIONS

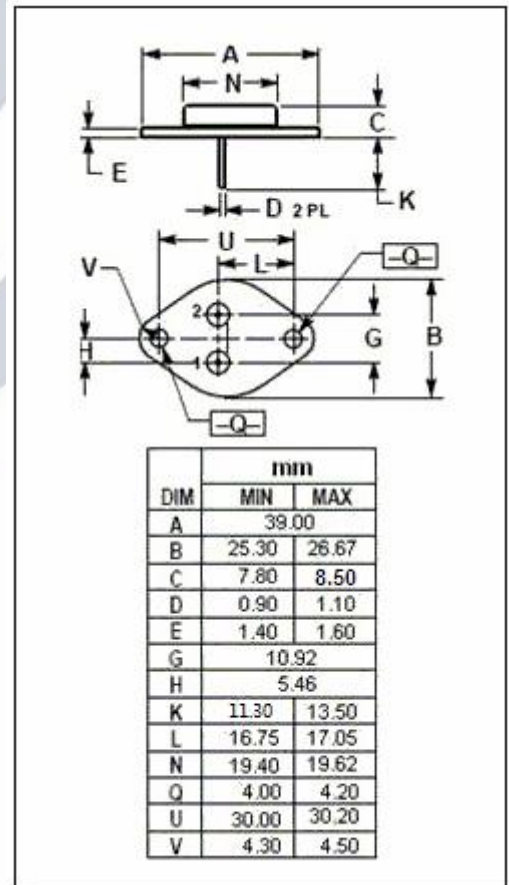
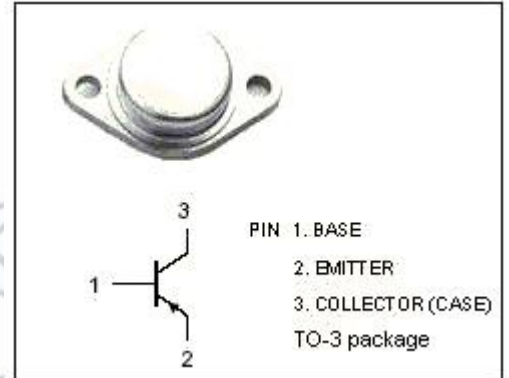
- Designed for general-purpose switching and amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-24	V
V_{EBO}	Emitter-Base Voltage	-20	V
I_C	Collector Current-Continuous	-6	A
P_C	Collector Power Dissipation @ $T_C=55^{\circ}C$	20	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.75	$^{\circ}C/W$



isc Silicon PNP Power Transistors**3AD53****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEQ(SUS)}	Collector-Emitter Sustaining Voltage	I _C = -50mA ; I _B = 0	-24		V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -4A; I _B = -0.4A		-1.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -4A ; V _{CE} = -4V		-1.5	V
I _{CEO}	Collector Cutoff Current	V _{CE} = -10V; I _B = 0		-10	mA
I _{CBO}	Collector Cutoff Current	V _{CB} = -20V; I _E = 0		-0.5	mA
h _{FE}	DC Current Gain	I _C = -4A ; V _{CE} = -2V	20	140	
f _T	Current Gain-Bandwidth Product	I _C = -0.5A ; V _{CE} = -10V; f _{test} = 1.0MHz	10		MHz